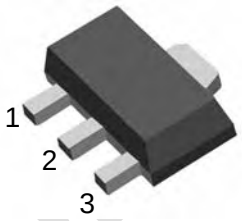
B772 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLETOR
3. EMITTER



FEATURES

Power dissipation

$P_{CM:}$ 500 mW (Tamb=25℃)

Collector current

$I_{CM:}$ -3 A

Collector-base voltage

$V_{(BR)CBO:}$ -40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

CLASSIFICATION OF $h_{FE(1)}$

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=-100μA , I_E=0	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA , I_B=0	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100 μA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V, I_E=0			-1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-30 V, I_B=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -2V, I_C= -1A	60		400	
	$h_{FE(2)}$	V_{CE}=-2V, I_C= -100mA	32			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-2A, I_B= -0.2A			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-2A, I_B= -0.2A			-1.5	V
Transition frequency	f_T	V_{CE}= -5V, $_C$=-0.1A f = 10MHz	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400